

J-FET INPUT LOW-OFFSET OPERATIONAL AMPLIFIER

The μPC4093 operational amplifier is a high-speed version of the μPC4091. NEC's unique high-speed PNP transistor ($f_T = 300$ MHz) in the output stage realizes a high slew rate of 25 V/ μ s under voltage-follower conditions without an oscillation problem. Zener-zap resistor trimming in the input stage produces excellent offset voltage and temperature drift characteristics.

With AC performance characteristics that are two times better than conventional bi-FET operation amplifiers, the μPC4093 is ideal for fast integrators, active filters, and other high-speed circuit applications.

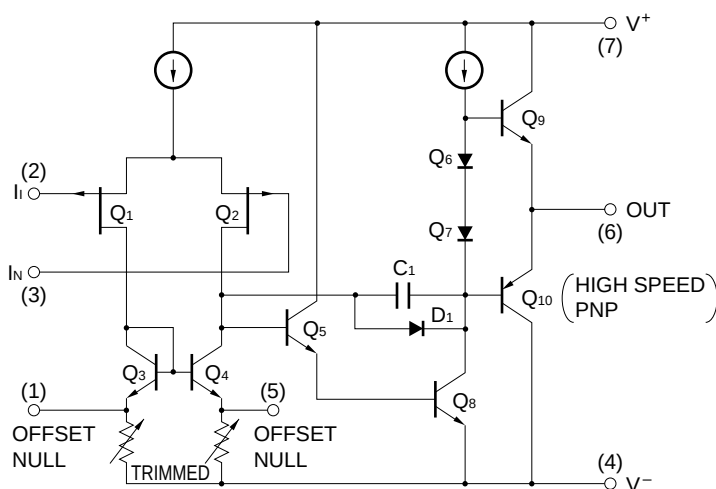
FEATURES

- Stable operation with 220 pF capacitive load
- Low input offset voltage and offset voltage null capability
 ± 2.5 mV (MAX.)
 ± 7 μ V/ $^{\circ}$ C (TYP.) temperature drift
- Very low input bias and offset currents
- Low noise : $e_n = 19$ nV/ $\sqrt{\text{Hz}}$ (TYP.)
- Output short circuit protection
- High input impedance ... J-FET Input Stage
- Internal frequency compensation
- High slew rate: 25 V/ μ s (TYP.)

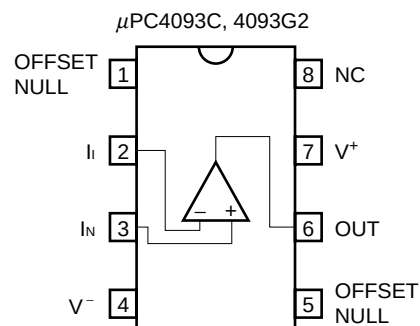
ORDERING INFORMATION

Part Number	Package
μPC4093C	8-pin plastic DIP (300 mil)
μPC4093G2	8-pin plastic SOP (225 mil)

EQUIVALENT CIRCUIT



PIN CONFIGURATION (Top View)



Remark NC : No Connection

The information in this document is subject to change without notice.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$)

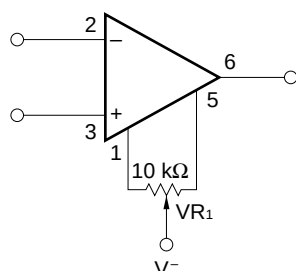
Parameter		Symbol	Ratings	Unit
Voltage between V^+ and V^- ^{Note 1}		$V^+ - V^-$	-0.3 to +36	V
Differential Input Voltage		V_{ID}	± 30	V
Input Voltage ^{Note 2}		V_I	$V^- - 0.3$ to $V^+ + 0.3$	V
Output Voltage ^{Note 3}		V_O	$V^- - 0.3$ to $V^+ + 0.3$	V
Power Dissipation	C Package ^{Note 4}	P_T	350	mW
	G2 Package ^{Note 5}		440	mW
Output Short Circuit Duration ^{Note 6}			Indefinite	sec
Operating Ambient Temperature		T_A	-20 to +80	$^\circ\text{C}$
Storage Temperature		T_{stg}	-55 to +125	$^\circ\text{C}$

Notes 1. Reverse connection of supply voltage can cause destruction.

2. The input voltage should be allowed to input without damage or destruction. Even during the transition period of supply voltage, power on/off etc., this specification should be kept. The normal operation will establish when the both inputs are within the Common Mode Input Voltage Range of electrical characteristics.
3. This specification is the voltage which should be allowed to supply to the output terminal from external without damage or destructive. Even during the transition period of supply voltage, power on/off etc., this specification should be kept. The output voltage of normal operation will be the Output Voltage Swing of electrical characteristics.
4. Thermal derating factor is $-5.0\text{ mW}/^\circ\text{C}$ when operating ambient temperature is higher than $55\text{ }^\circ\text{C}$.
5. Thermal derating factor is $-4.4\text{ mW}/^\circ\text{C}$ when operating ambient temperature is higher than $25\text{ }^\circ\text{C}$.
6. Pay careful attention to the total power dissipation not to exceed the absolute maximum ratings, Note 4 and Note 5.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	$V^\pm$	± 5		± 16	V
Output Current	I_O			± 10	mA
Capacitive Load ($A_v = +1$, $R_f = 0\text{ }\Omega$)	C_L			220	pF

OFFSET VOLTAGE NULL CIRCUIT

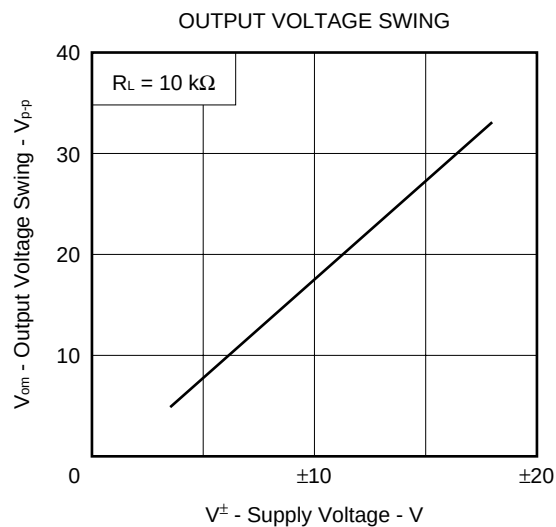
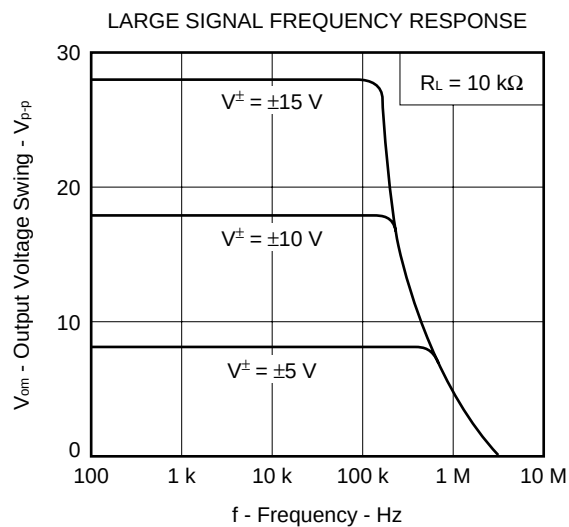
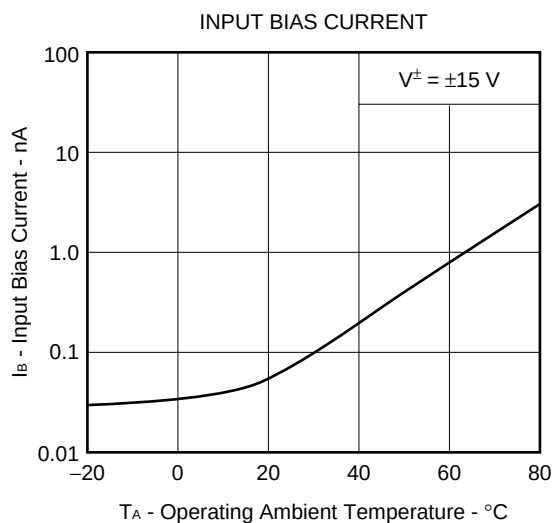
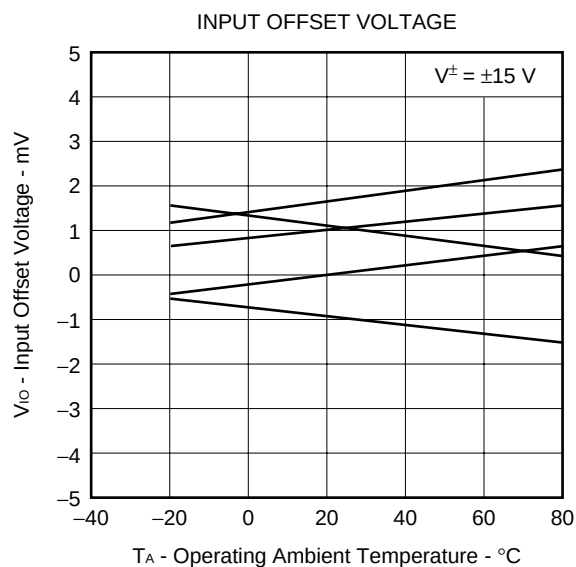
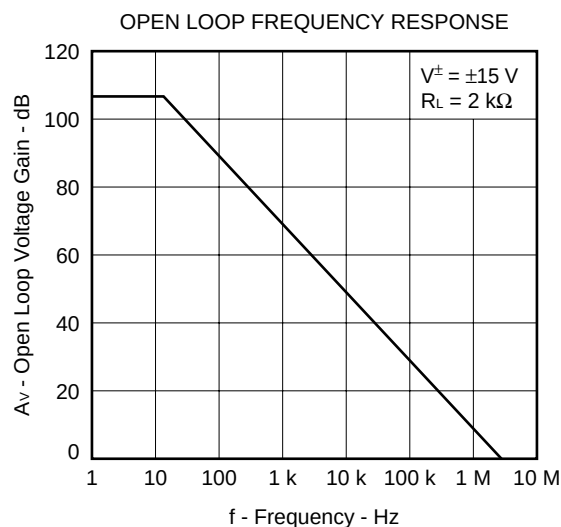
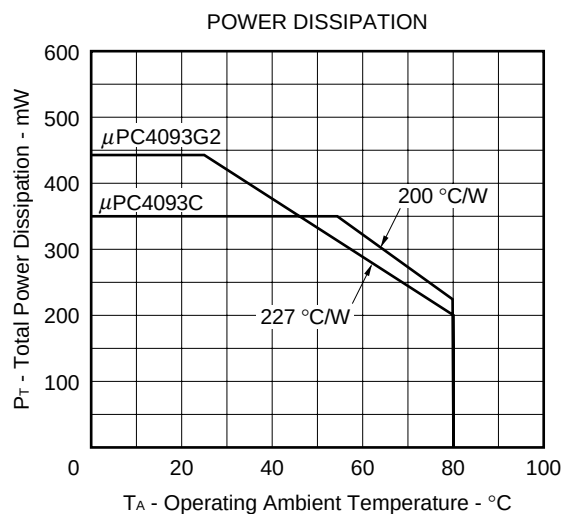
Remark The OFFSET NULL pins should be left open or connected to V^- via a resistor as shown in the left figure. Don't connect to any lines other than V^- , otherwise malfunction, degradation, or failure may occur.

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, $V^\pm = \pm 15\text{ V}$)

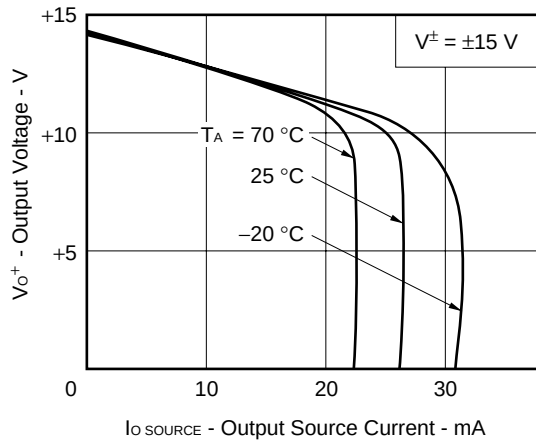
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input Offset Voltage	V_{IO}	$R_S \leq 50\ \Omega$		± 1	± 2.5	mV
Input Offset Current ^{Note 7}	I_{IO}			± 25	± 100	pA
Input Bias Current ^{Note 7}	I_B			50	200	pA
Large Signal Voltage Gain	A_V	$R_L \geq 2\text{ k}\Omega$, $V_O = \pm 10\text{ V}$	25000	200000		
Supply Current	I_{CC}	$I_O = 0\text{ A}$		2.5	3.4	mA
Common Mode Rejection Ratio	CMR		70	100		dB
Supply Voltage Rejection Ratio	SVR		70	100		dB
Output Voltage Swing	V_{om}	$R_L \geq 10\text{ k}\Omega$	± 12	+14.0 -13.3		V
		$R_L \geq 2\text{ k}\Omega$	± 10	+13.5 -12.8		V
Common Mode Input Voltage Range	V_{ICM}		± 11	+14 -12		V
Slew Rate	SR	$A_V = 1$		25		V/ μ s
Unity Gain Frequency	f_{unity}			6		MHz
Input Equivalent Noise Voltage Density	e_n	$R_S = 100\ \Omega$, $f = 1\text{ kHz}$		19		nV/ $\sqrt{\text{Hz}}$
Input Offset Voltage	V_{IO}	$R_S \leq 50\ \Omega$, $T_A = -20\text{ to }+70\text{ }^\circ\text{C}$			± 5	mV
Average V_{IO} Temperature Drift	$\Delta V_{IO}/\Delta T$	$T_A = -20\text{ to }+70\text{ }^\circ\text{C}$		± 7		$\mu\text{V}/^\circ\text{C}$
Input Offset Current ^{Note 7}	I_{IO}	$T_A = -20\text{ to }+70\text{ }^\circ\text{C}$			± 2	nA
Input Bias Current ^{Note 7}	I_B	$T_A = -20\text{ to }+70\text{ }^\circ\text{C}$			7	nA

Notes 7. Input bias currents flow into IC. Because each currents are gate leak current of P-channel J-FET on input stage. And that are temperature sensitive. Short time measuring method is recommendable to maintain the junction temperature close to the operating ambient temperature.

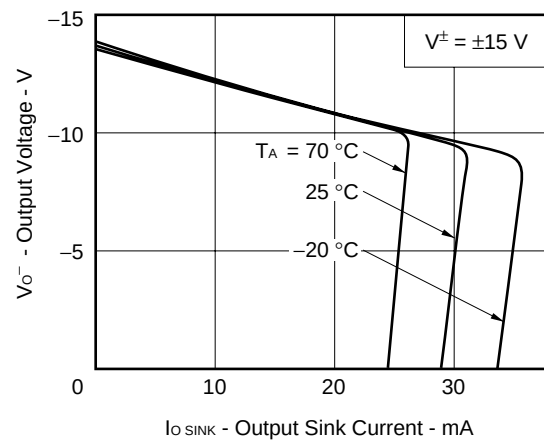
TYPICAL PERFORMANCE CHARACTERISTICS ($T_A = 25^\circ\text{C}$, TYP.)



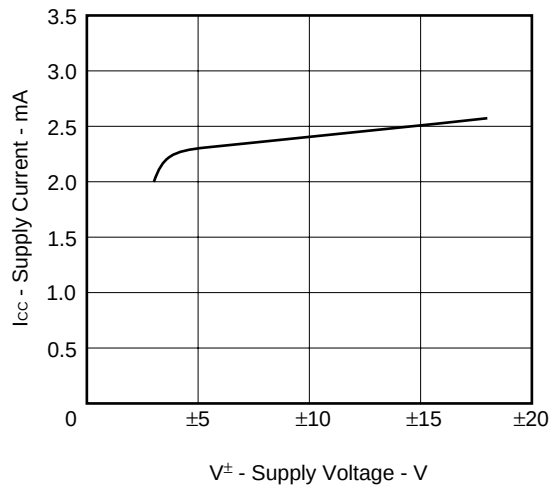
OUTPUT SOURCE CURRENT LIMIT



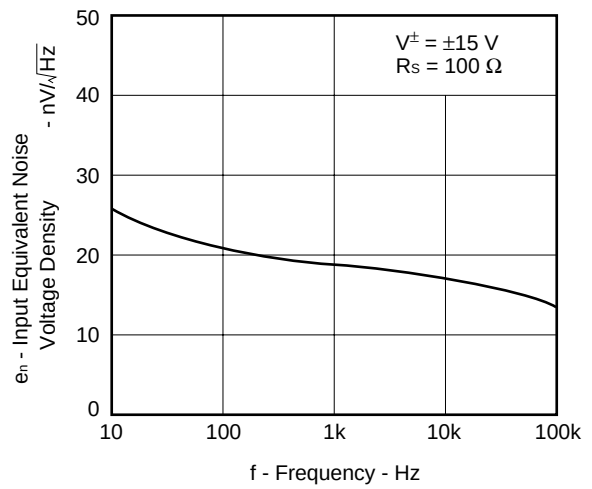
OUTPUT SINK CURRENT LIMIT



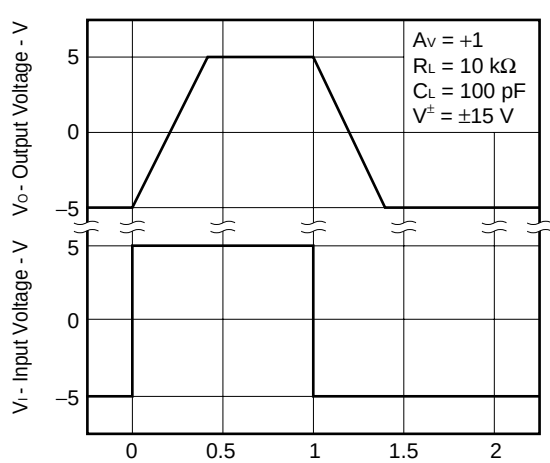
SUPPLY CURRENT



INPUT EQUIVALENT NOISE VOLTAGE DENSITY

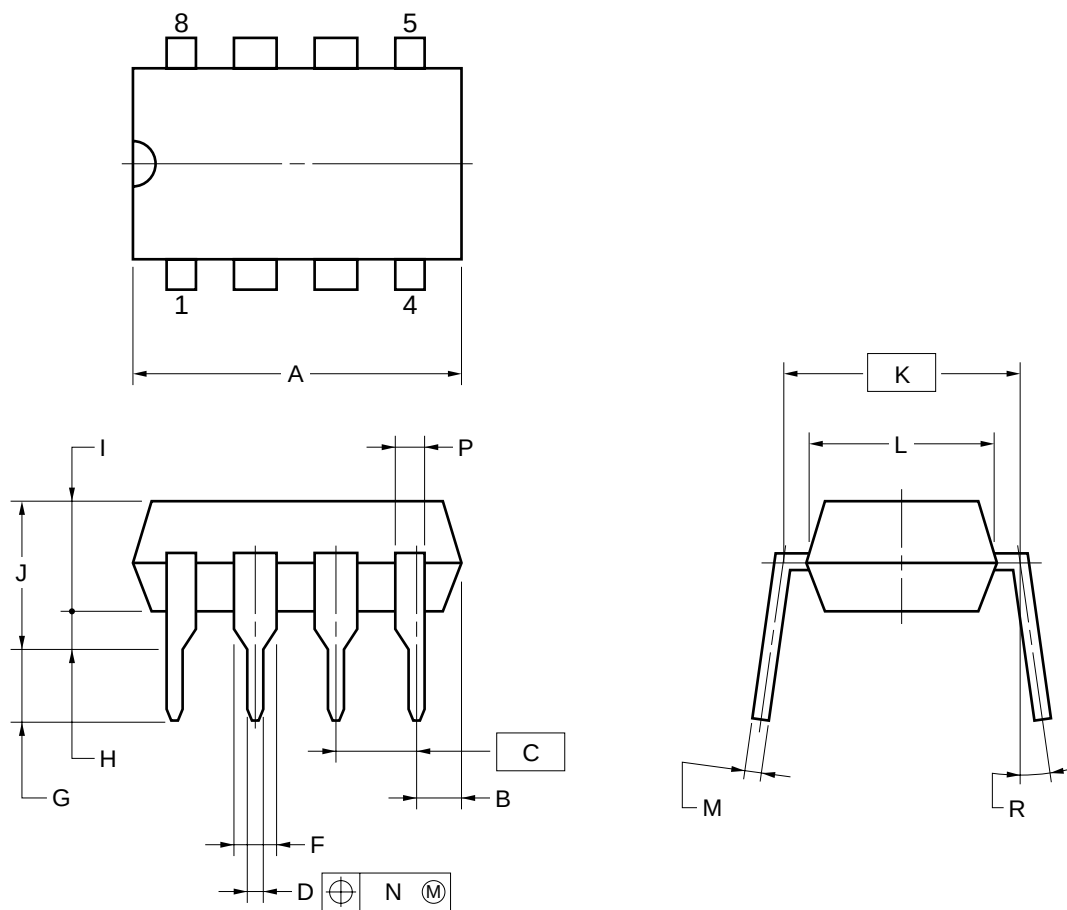


VOLTAGE FOLLOWER PULSE RESPONSE



PACKAGE DRAWINGS

8PIN PLASTIC DIP (300 mil)



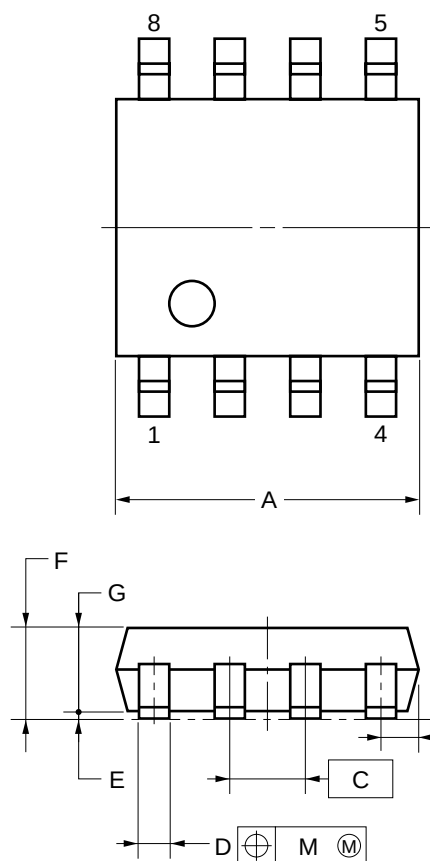
NOTES

- 1) Each lead centerline is located within 0.25 mm (0.01 inch) of its true position (T.P.) at maximum material condition.
- 2) Item "K" to center of leads when formed parallel.

ITEM	MILLIMETERS	INCHES
A	10.16 MAX.	0.400 MAX.
B	1.27 MAX.	0.050 MAX.
C	2.54 (T.P.)	0.100 (T.P.)
D	0.50±0.10	0.020 ^{+0.004} _{-0.005}
F	1.4 MIN.	0.055 MIN.
G	3.2±0.3	0.126±0.012
H	0.51 MIN.	0.020 MIN.
I	4.31 MAX.	0.170 MAX.
J	5.08 MAX.	0.200 MAX.
K	7.62 (T.P.)	0.300 (T.P.)
L	6.4	0.252
M	0.25 ^{+0.10} _{-0.05}	0.010 ^{+0.004} _{-0.003}
N	0.25	0.01
P	0.9 MIN.	0.035 MIN.
R	0~15°	0~15°

P8C-100-300B,C-1

8 PIN PLASTIC SOP (225 mil)



NOTE

Each lead centerline is located within 0.12 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	$5.2^{+0.17}_{-0.20}$
B	0.78 MAX.
C	1.27 (T.P.)
D	$0.42^{+0.08}_{-0.07}$
E	0.1 ± 0.1
F	1.59 ± 0.21
G	1.49
H	6.5 ± 0.3
I	4.4 ± 0.15
J	1.1 ± 0.2
K	$0.17^{+0.08}_{-0.07}$
L	0.6 ± 0.2
M	0.12
N	0.10
P	$3^{\circ+7^{\circ}}_{-3^{\circ}}$

S8GM-50-225B-5

RECOMMENDED SOLDERING CONDITIONS

When soldering this product, it is highly recommended to observe the conditions as shown below. If other soldering processes are used, or if the soldering is performed under different conditions, please make sure to consult with our sales offices.

For more details, refer to our document "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL"(C10535E).

Type of Surface Mount Device

μPC4093G2: 8-pin plastic SOP (225 mil)

Process	Conditions	Symbol
Infrared Ray Reflow	Peak temperature: 230 °C or below (Package surface temperature), Reflow time: 30 seconds or less (at 210 °C or higher), Maximum number of reflow processes: 1 time.	IR30-00-1
Vapor Phase Soldering	Peak temperature: 215 °C or below (Package surface temperature), Reflow time: 40 seconds or less (at 200 °C or higher), Maximum number of reflow processes: 1 time.	VP15-00-1
Wave Soldering	Solder temperature: 260 °C or below, Flow time: 10 seconds or less, Maximum number of flow processes: 1 time, Pre-heating temperature: 120 °C or below (Package surface temperature).	WS60-00-1
Partial Heating Method	Pin temperature: 300 °C or below, Heat time: 3 seconds or less (Per each side of the device).	—

Caution Apply only one kind of soldering condition to a device, except for "partial heating method", or the device will be damaged by heat stress.

Type of Through-hole Device

μPC4093C: 8-pin plastic DIP (300 mil)

Process	Conditions
Wave Soldering (only to leads)	Solder temperature: 260 °C or below, Flow time: 10 seconds or less.
Partial Heating Method	Pin temperature: 300 °C or below, Heat time: 3 seconds or less (per each lead).

Caution For through-hole device, the wave soldering process must be applied only to leads, and make sure that the package body does not get jet soldered.

REFERENCE DOCUMENTS

QUALITY GRADES ON NEC SEMICONDUCTOR DEVICES	C11531E
SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL	C10535E
NEC IC PACKAGE MANUAL (CD-ROM)	C13388E
GUIDE TO QUALITY ASSURANCE FOR SEMICONDUCTOR DEVICES	MEI-1202
SEMICONDUCTORS SELECTION GUIDE	X10679E
NEC SEMICONDUCTOR DEVICE RELIABILITY/QUALITY CONTROL SYSTEM (STANDARD LINEAR IC)	IEI-1212

[MEMO]

[MEMO]

[MEMO]

The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.

NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from use of a device described herein or any other liability arising from use of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC Corporation or others.

While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customers must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.

NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

Anti-radioactive design is not implemented in this product.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.